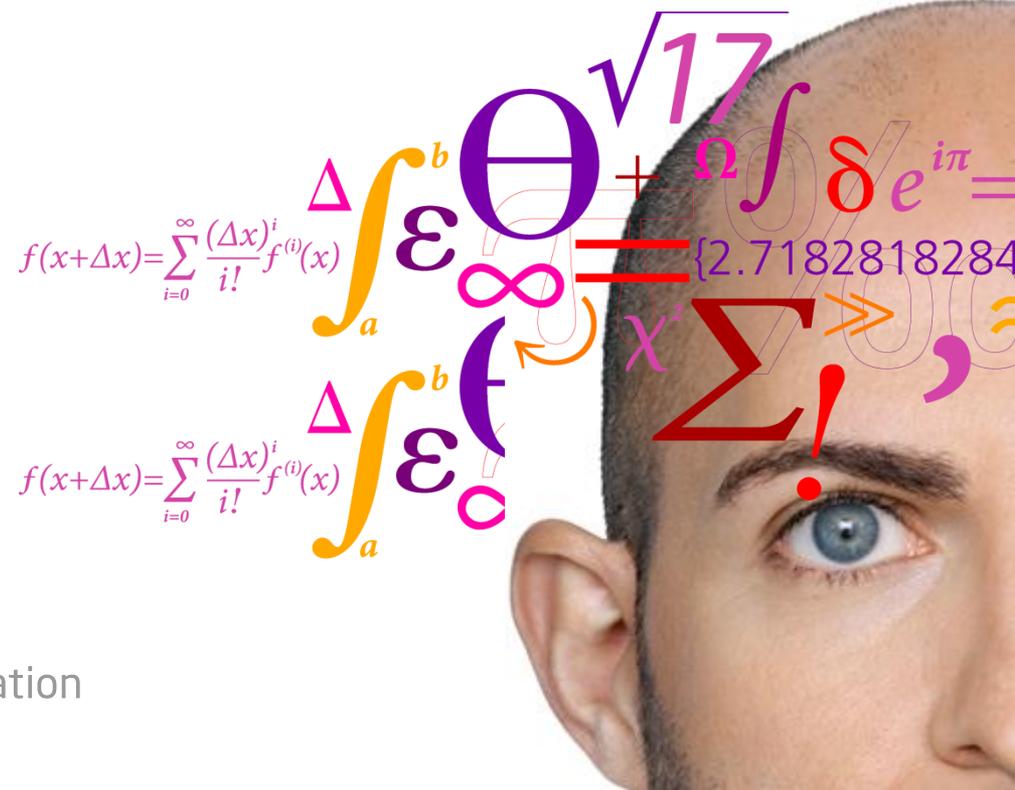


# Lithography Tool Package

Introduction to Lithography



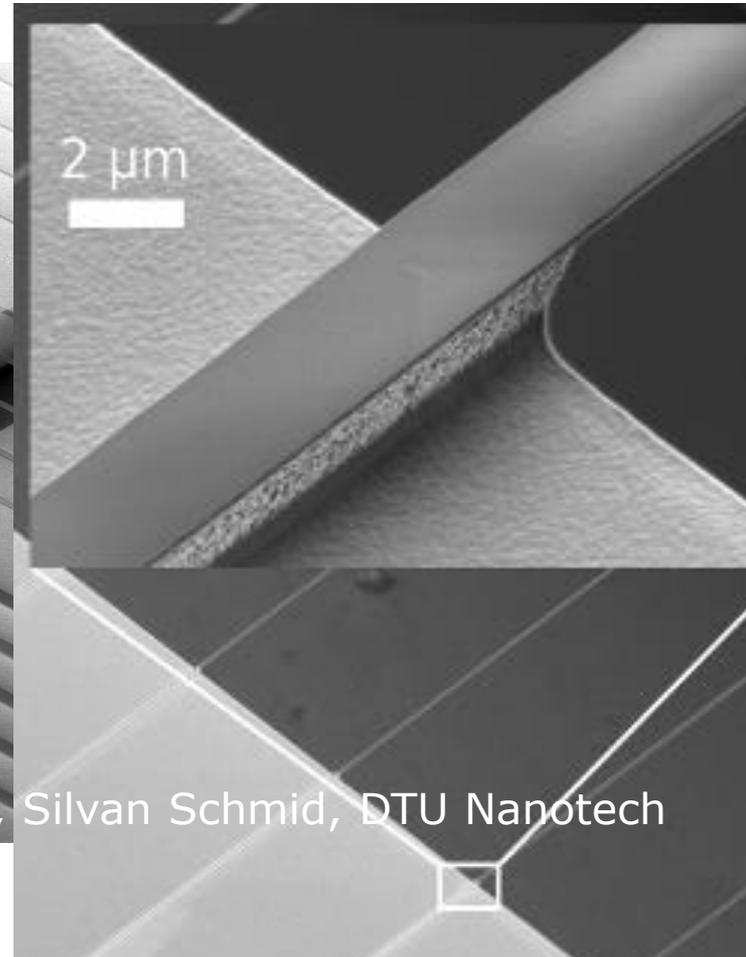
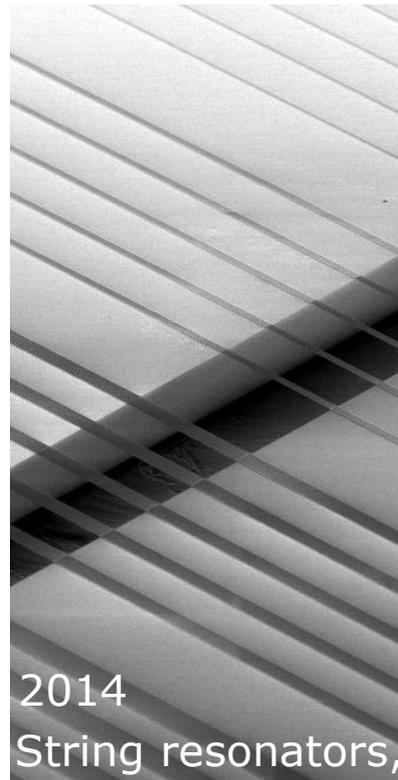
DTU Danchip

National Center for Micro- and Nanofabrication

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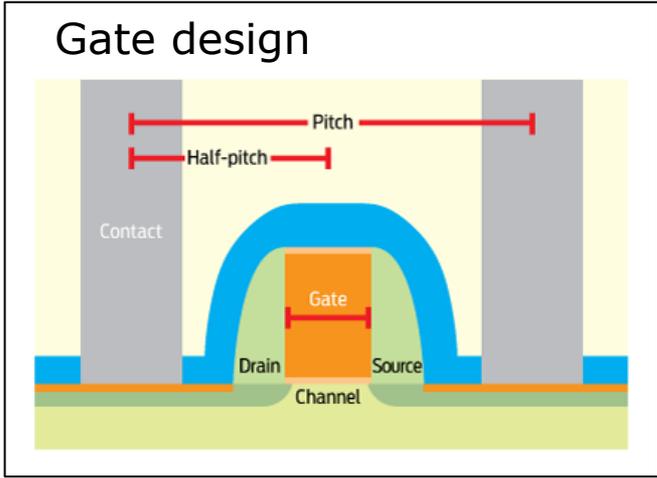
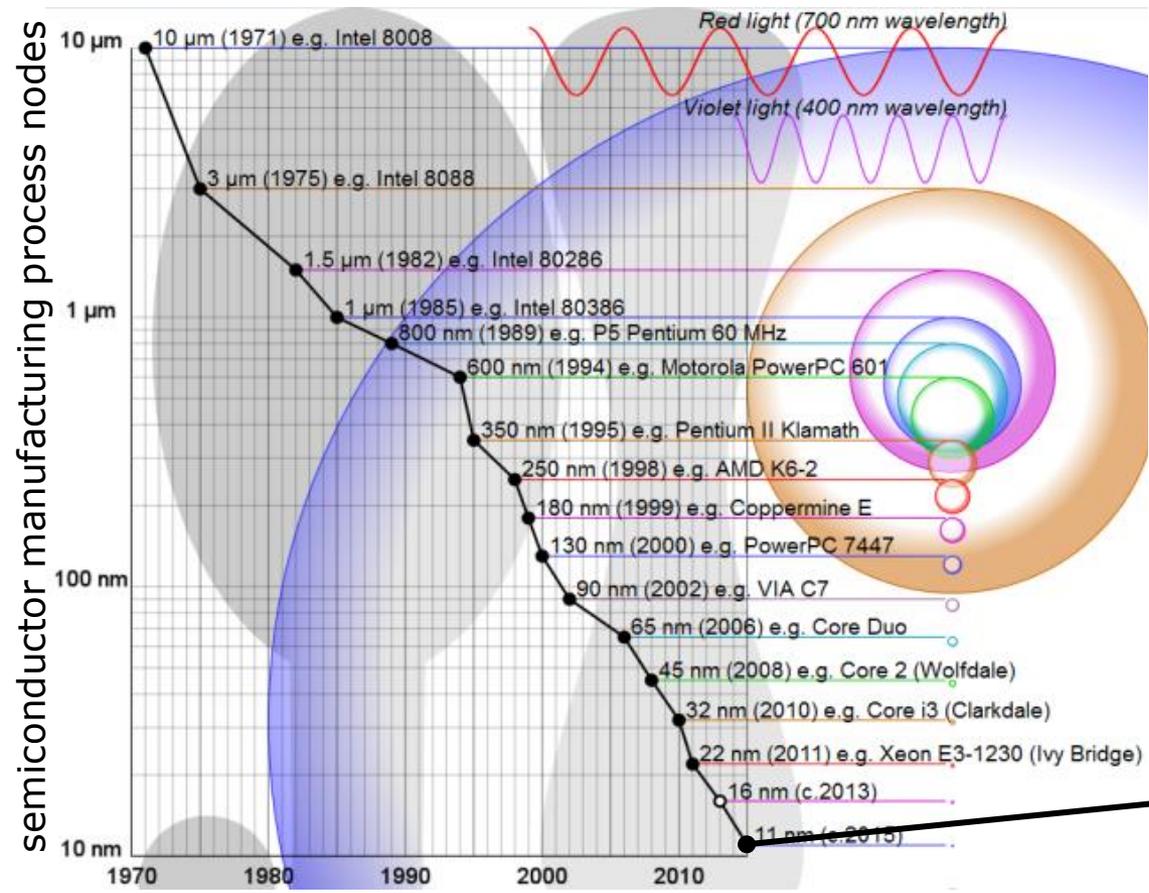
# Lithography

**Lithography:** from Ancient Greek λίθος, *lithos*, meaning "stone", and γράφειν, *graphein*, meaning "to write".



# Lithography: Why?

## → Miniaturization of semiconductor devices



1990'ies: node = half pitch  
 Now: node  $\lesssim$  gate length



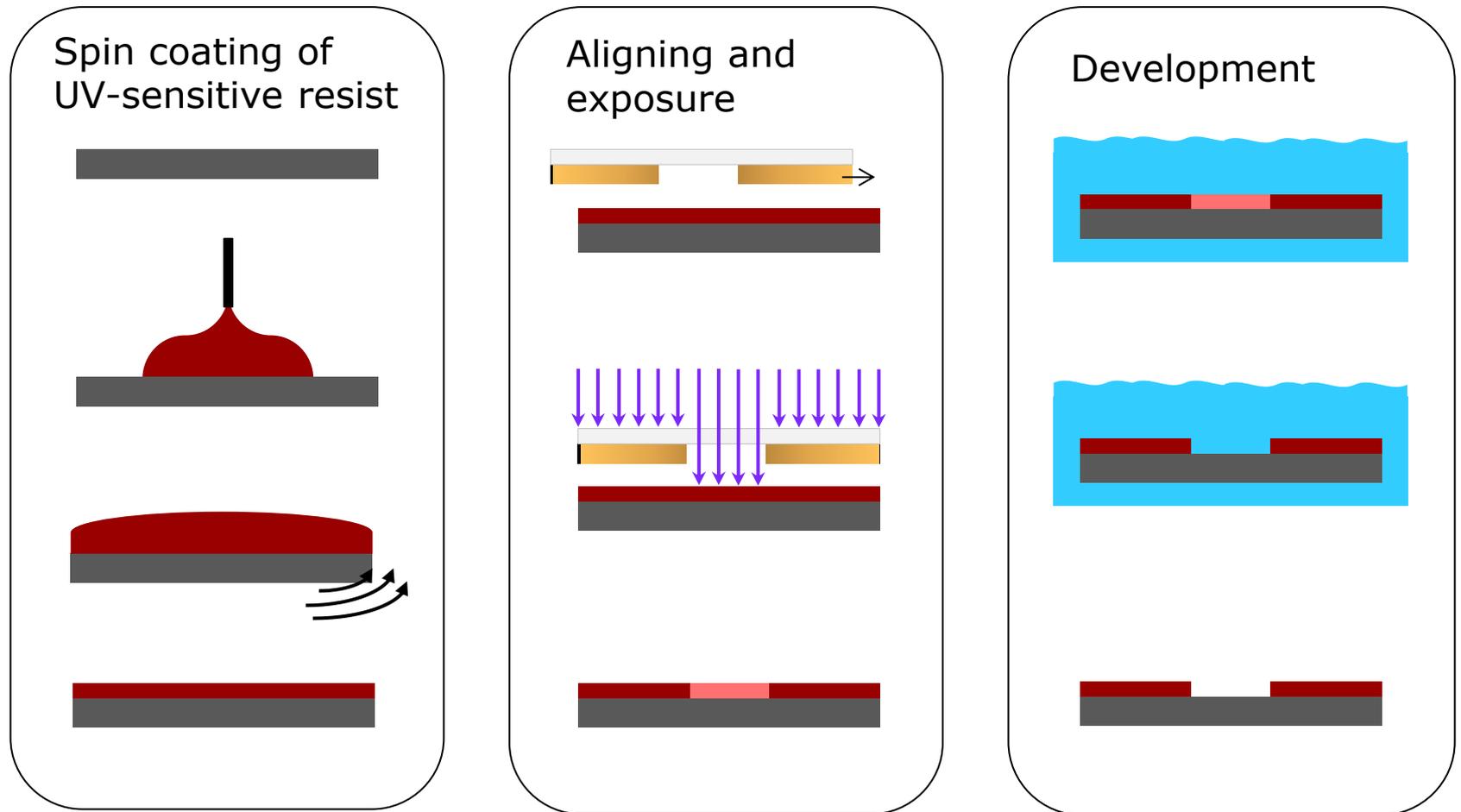
[https://en.wikipedia.org/wiki/Semiconductor\\_device\\_fabrication](https://en.wikipedia.org/wiki/Semiconductor_device_fabrication)

# Lithography: methods

Technology	Exposure Source	Wavelength	Minimum Resolution [nm]
UV Contact Lithography	Hg vapor lamp	365 nm	1500
UV Projection Lithography	Hg vapor lamp	365 nm	800 – 350
Deep-UV Projection Lithography	KrF excimer laser	248 nm	250 – 90
Deep-UV Immersion Lithography	ArF excimer laser	193 nm	110 – 38
Extreme-UV Projection Lithography	IR Laser-produced Sn plasma EUV	13.5 nm	< 20
Electron Beam Lithography	Field-emission electron gun (100 keV)	0.39 nm	< 10

Available at DTU Danchip

# UV lithography: process

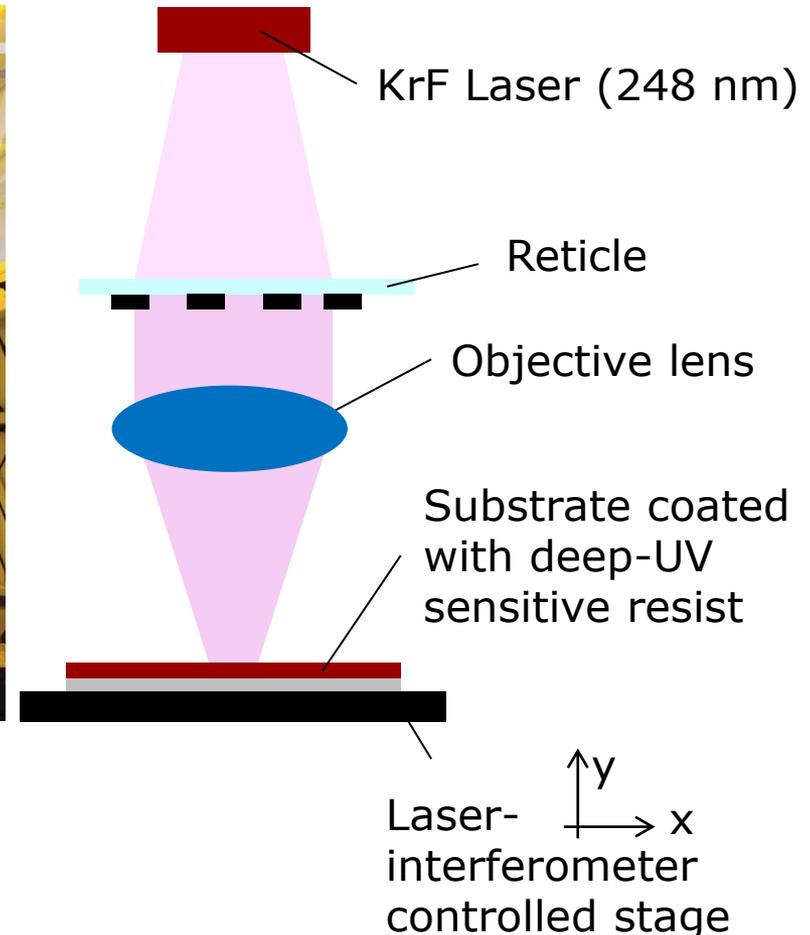


# UV lithography: equipment

- Coating:
  - 2 (3) automatic spin coaters
  - 4 manual spin coaters
  - 1 spray coater
- Exposure:
  - 3 mask aligners
  - 1 UV flood exposure source
- Development:
  - 2 submersion developer benches
  - 1 automatic puddle developer
  - 1 manual spray/puddle developer
- Auxiliary:
  - HMDS priming ovens
  - Hotplates
  - Lift-off benches
  - Resist strip bench



# DUV Stepper Lithography: principle

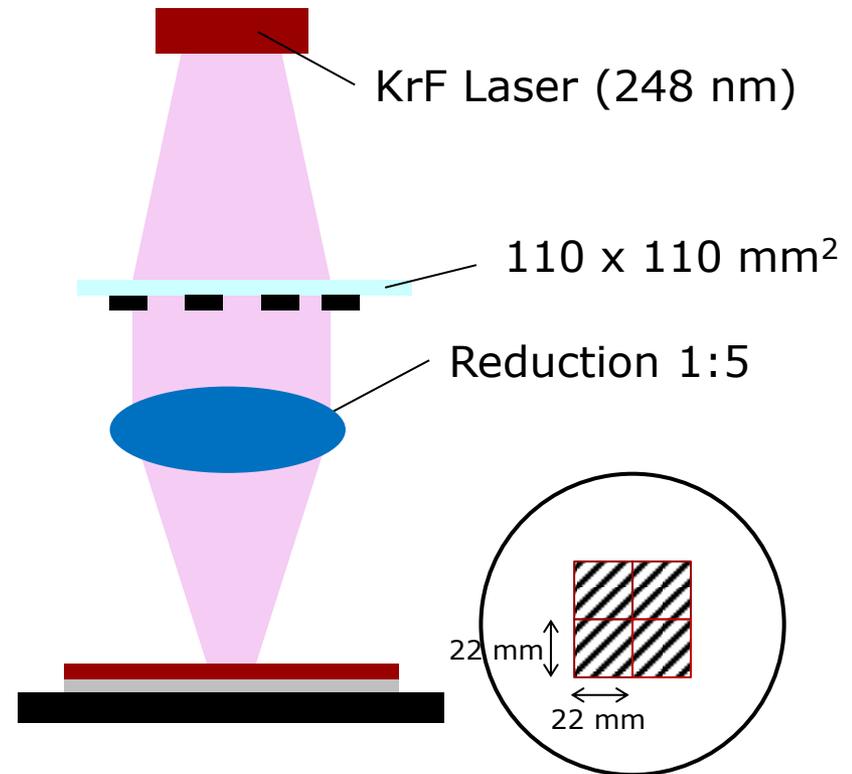


Auxiliary equipment:

- Automatic spin coater
- Automatic developer

# DUV Stepper Lithography: performance

<b>CANON FPA-3000 EX-4</b>	
Light Source	248 nm KrF Laser
Objective Lens	Reduction 1:5
Writing field (Field size on substrate level)	22 mm x 22 mm
Field Stitching accuracy	50 nm
Overlay accuracy	30 nm
Resolution	160-250 nm depending on pitch and pattern

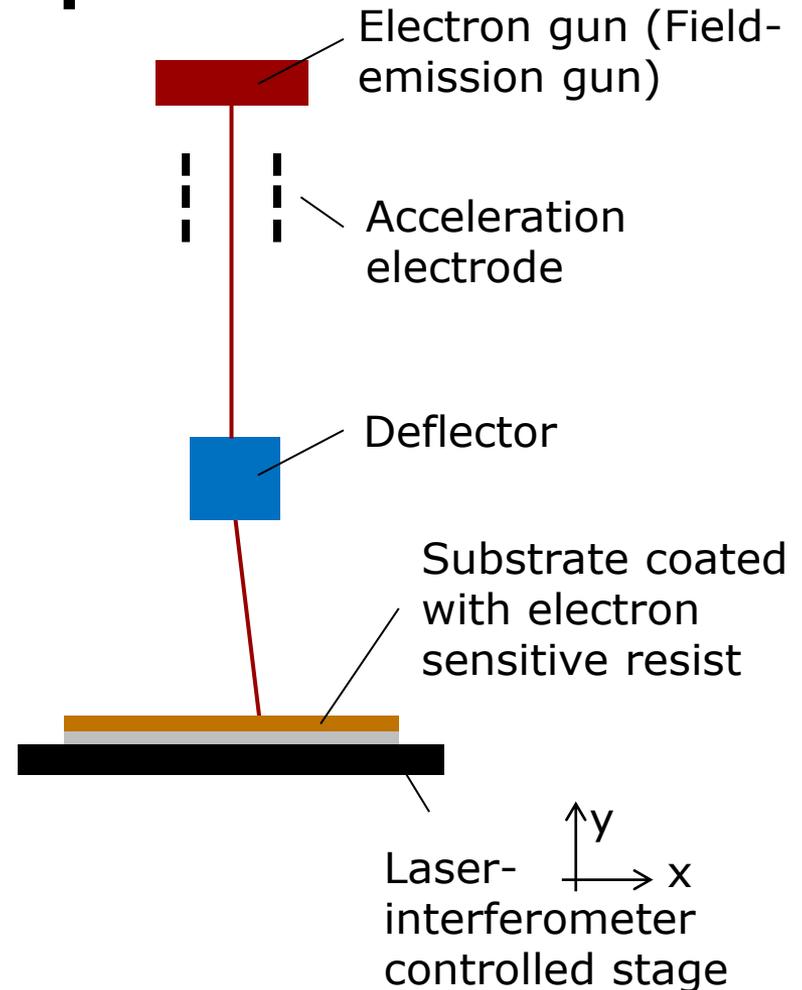


# E-beam Lithography: principle



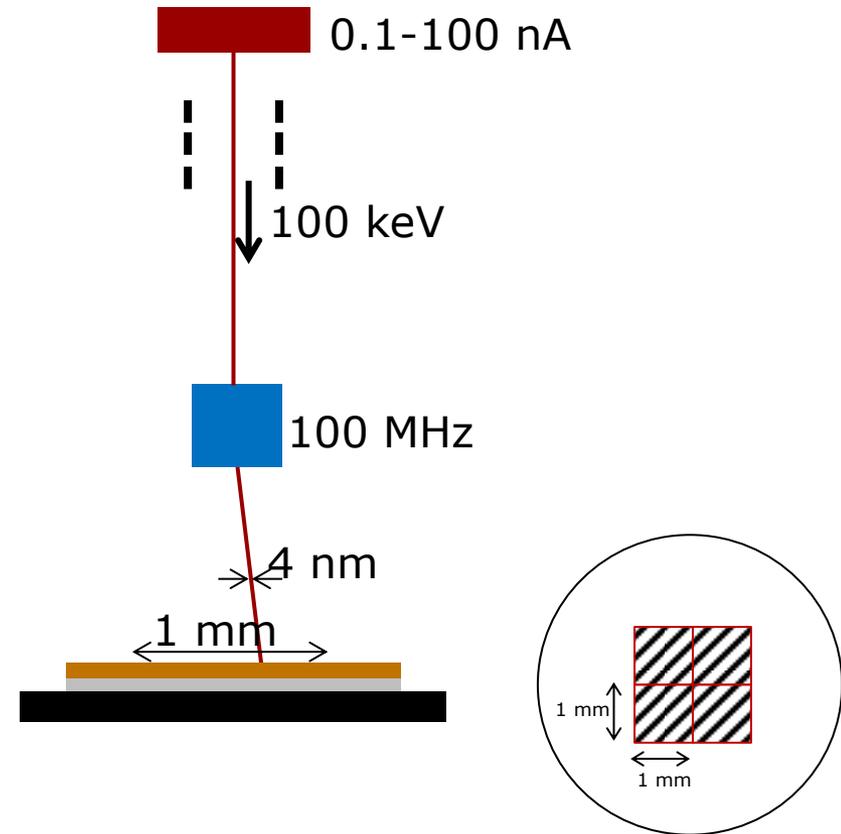
Auxiliary equipment:

- Manual spin coater(s)
- Fume hood for development



# E-beam Lithography: performance

<b>JEOL JBX-9500FSZ</b>	
Acceleration voltage	100 keV
Maximum scan frequency	100 MHz
Beam current	0.1-100 nA
Beam Diameter at substrate level	4 nm (@ 0.1 nA)
Writing field (maximum deflection)	1 mm x 1 mm
Field stitching accuracy	< 5 nm
Overlay Accuracy	< 10 nm
Resolution	Down to 10 nm



# Lithography: comparison

	<b>UV Lithography</b>	<b>DUV Stepper Lithography</b>	<b>E-beam Lithography</b>
Minimum Resolution	~1.5 $\mu\text{m}$	~220 nm	~10 nm
Process time (4" wafer)	<ul style="list-style-type: none"> <li>• ~2 min load and unload</li> <li>• ~10 s per exposure</li> </ul>	<ul style="list-style-type: none"> <li>• ~10 min load and unload</li> <li>• ~1 s per field exposure</li> </ul>	<ul style="list-style-type: none"> <li>• ~1 h of machine calibration + substrate load and unload</li> <li>• A pattern area of 1 <math>\text{cm}^2</math> takes ~8 h to expose with a beam current of 10 nA and a dose of 300 <math>\mu\text{C}/\text{cm}^2</math></li> </ul>
Throughput (4" wafer)	~25 wafer/hour	$\geq 6$ wafer/hour (much higher for 6")	$\leq 1$ wafer/hour
Training	Litho TPT + separate trainings	Processed by DTU Danchip	Only available for Ph.D. and up

# Litho Tool Package Training

- First process theory, then equipment training

## **Today** (once a month):

- The hardware, theory, physics, chemistry, steps, and process parameters involved in UV lithography

## **Later** (once a week, max. 6 persons per week):

- A full day of UV lithography process and equipment training, covering
  - Spin coating
  - Exposure and alignment
  - Development
  - Characterization of the results

If you prepare yourself and perform well, there is a chance you will be fully authorized on three pieces of equipment central to UV lithography processing at the end of the Litho TPT

# Outline

## 1. Introduction

- UV lithography
- DUV Stepper
- E-beam writer

## 2. Spin coating

- Resist composition
- Pre-treatment
- Principle
- Softbake
- Spin curve

## 3. Exposure

- Hardware
- Process parameters
- Resolution
- Alignment
- Photo-chemistry

## 4. Development

- Principle
- Effects
- Resist contrast
- Pattern transfer
- Post-processing

## 5. Process effects and examples

- Inspection methods
- Process effects
- Real life process examples

